What is claimed is:

1. A semiconductor processing module comprising:

a housing adapted to enclose a semiconductor wafer;

an ultraviolet radiation source disposed within the housing; and

a treatment medium disposed within the housing.

2. The module of claim 1, wherein the ultraviolet radiation source comprises an ultraviolet lamp.

3. The module of claim 1, wherein the treatment medium comprises ambient air.

4. The module of claim 1, wherein the treatment medium comprises oxygen.

5. The module of claim 1, wherein the treatment medium comprises ozone.

6. The module of claim 1, further comprising a medium supply system disposed within the housing.

7. The module of claim 6, wherein the medium supply system comprises a gas inlet.

8. The module of claim 6, wherein the medium supply system comprises an ozone generator.

9. The module of claim 1, further comprising a medium conditioning system disposed within the housing.

10. The module of claim 9, further comprising a medium supply system disposed within the medium conditioning system.

11. The module of claim 9, wherein the medium conditioning system is adapted to induce a partial vacuum within the housing.

12. The module of claim 9, wherein the treatment medium is a vacuum induced by the medium conditioning system.

13. The module of claim 9, wherein the medium conditioning system comprises a filtration system.

14. A method of removing contaminants from a semiconductor substrate, comprising the steps of:

providing a housing adapted to enclose a semiconductor substrate;

providing an ultraviolet radiation source disposed within the housing;

providing a treatment medium disposed within the housing;

enclosing a semiconductor substrate within the housing;

exposing the semiconductor substrate to the treatment medium; and

utilizing the ultraviolet radiation source to expose the semiconductor substrate to ultraviolet radiation.

15. The method of claim 14, wherein the step of providing an ultraviolet radiation source further comprises providing an ultraviolet lamp.

16. The method of claim 14, wherein the step of providing a treatment medium further comprises providing ambient air.

17. The method of claim 16, wherein the step of providing a treatment medium further comprises providing ambient air in a partial vacuum.

18. The method of claim 14, wherein the step of providing a treatment medium further comprises providing a vacuum.

19. The method of claim 14, wherein the step of providing a treatment medium further comprises providing a treatment medium comprising mostly oxygen.

20. The method of claim 19, wherein the step of providing a treatment medium further comprises providing a treatment medium comprising mostly oxygen in a partial vacuum.

21. The method of claim 14, wherein the step of providing a treatment medium further comprises providing a treatment medium comprising ozone.

22. The method of claim 21, wherein the step of providing a treatment medium comprising ozone further comprises providing an ozone generator to supply ozone within the housing.

23. The method of claim 21, wherein the step of providing a treatment medium further comprises providing a treatment medium comprising ozone in a partial vacuum.

24. The method of claim 14, further comprising the step of growing a layer of oxide on the surface of the substrate.

25. The method of claim 24, wherein the step of growing a layer of oxide further comprises controlling oxide growth by adjusting time and intensity of the ultraviolet radiation exposure.

26. The method of claim 24, wherein the step of growing a layer of oxide further comprises controlling oxide growth by adjusting composition of the treatment medium.

27. A system for remediating organic contaminants from a copper seed layer deposited on an upper surface of a semiconductor wafer, the system comprising:

a housing adapted to receive and enclose the semiconductor wafer;

an ultraviolet radiation source disposed within the housing and adapted to expose the semiconductor wafer to ultraviolet radiation;

an ozone generator adapted to supply ozone into the housing as a treatment medium for the semiconductor wafer; and

a conditioning system disposed within the housing and adapted to filter contaminants from the ozone.